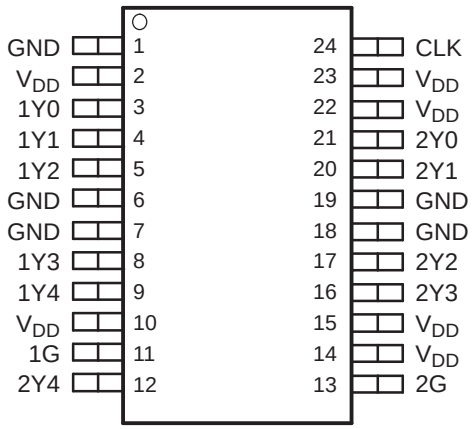
2.5-V TO 3.3-V HIGH-PERFORMANCE CLOCK BUFFER

Check for Samples: CDCVF2310-EP

FEATURES

- **High-Performance 1:10 Clock Driver**
- **Operates up to 200 MHz at V_{DD} 3.3 V**
- **Pin-to-Pin Skew < 100 ps at V_{DD} 3.3 V**
- **V_{DD} Range: 2.3 V to 3.6 V**
- **Output Enable Glitch Suppression**
- **Distributes One Clock Input to Two Banks of Five Outputs**
- **25-Ω On-Chip Series Damping Resistors**
- **Packaged in 24-Pin TSSOP**

PW PACKAGE
(TOP VIEW)



APPLICATIONS

- **General-Purpose Applications**

SUPPORTS DEFENSE, AEROSPACE, AND MEDICAL APPLICATIONS

- **Controlled Baseline**
- **One Assembly and Test Site**
- **One Fabrication Site**
- **Available in Military (–55°C to 125°C) Temperature Range** (1)
- **Extended Product Life Cycle**
- **Extended Product-Change Notification**
- **Product Traceability**

(1) Custom temperature ranges available

DESCRIPTION

The CDCVF2310 is a high-performance, low-skew clock buffer that operates up to 200 MHz. Two banks of five outputs each provide low-skew copies of CLK. After power up, the default state of the outputs is low regardless of the state of the control pins. For normal operation, the outputs of bank 1Y[0:4] or 2Y[0:4] can be placed in a low state when the control pins (1G or 2G, respectively) are held low and a negative clock edge is detected on the CLK input. The outputs of bank 1Y[0:4] or 2Y[0:4] can be switched into the buffer mode when the control pins (1G and 2G) are held high and a negative clock edge is detected on the CLK input. The device operates in a 2.5-V and 3.3-V environment. The built-in output enable glitch suppression ensures a synchronized output enable sequence to distribute full period clock signals.

The CDCVF2310 is characterized for operation from –55°C to 125°C.

Table 1. ORDERING INFORMATION(1)

T_J	PACKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING	VID NUMBER
–55°C to 125°C	TSSOP - PW	CDCVF2310MPWREP	CKV2310EP	V62/13603-01XE
		CDCVF2310MPWEP	CKV2310EP	V62/13603-01XE-T

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

FUNCTIONAL BLOCK DIAGRAM

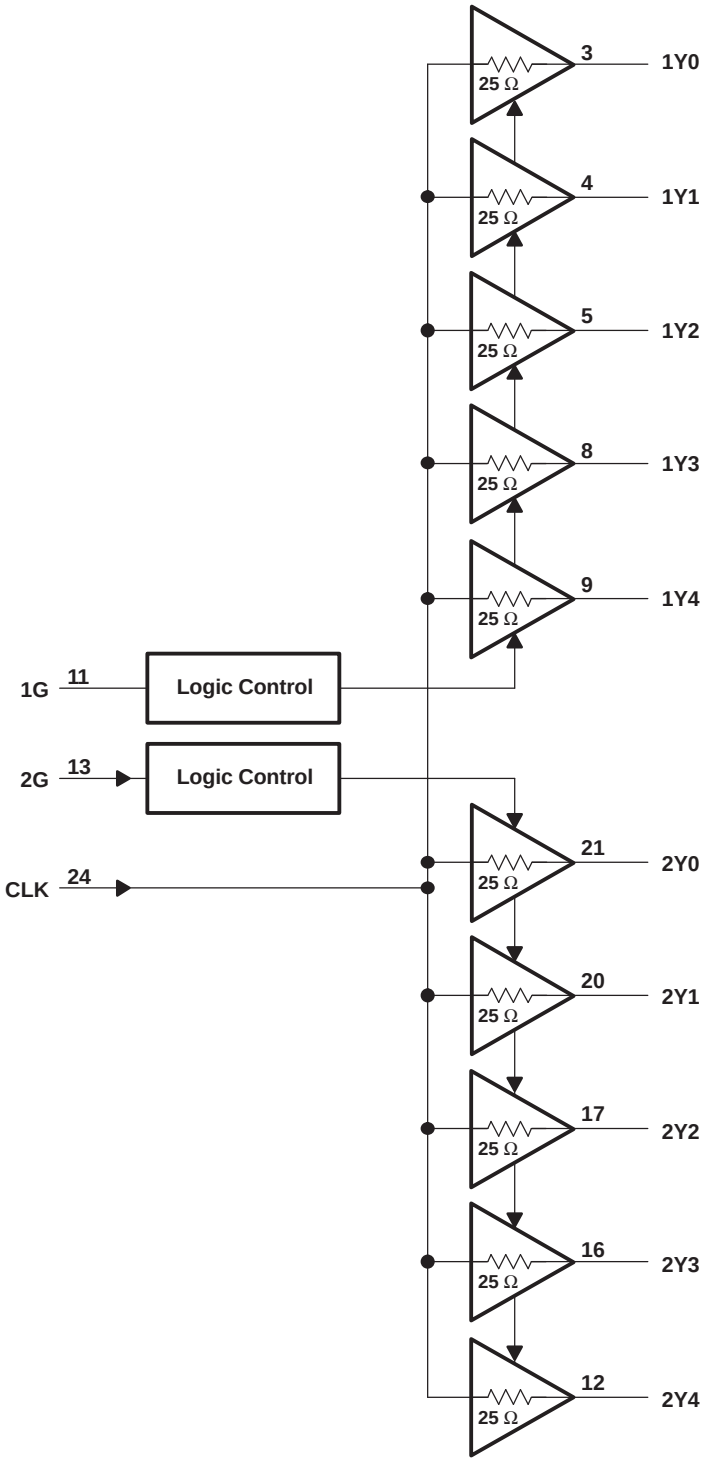


Table 2. FUNCTION TABLE

INPUT			OUTPUT	
1G	**2G**	**CLK**	**1Y[0:4]**	**2Y[0:4]**
L	L	↓	L	L
H	L	↓	CLK(1)	L
L	H	↓	L	CLK(1)
H	H	↓	CLK(1)	CLK(1)

(1) After detecting one negative edge on the CLK input, the output follows the input CLK if the control pin is held high.

Terminal Functions

TERMINAL		I/O	DESCRIPTION
NAME	**NO.**		
1G	11	I	Output enable control for 1Y[0:4] outputs. This output enable is active-high, meaning the 1Y[0:4] clock outputs follow the input clock (CLK) if this pin is logic high.
2G	13	I	Output enable control for 2Y[0:4] outputs. This output enable is active-high, meaning the 2Y[0:4] clock outputs follow the input clock (CLK) if this pin is logic high.
1Y[0:4]	3, 4, 5, 8, 9	O	Buffered output clocks
2Y[0:4]	21, 20, 17, 16, 12	O	Buffered output clocks
CLK	24	I	Input reference frequency
GND	1, 6, 7, 18, 19		Ground
V_{DD}	2, 10, 14, 15, 22, 23		DC power supply, 2.3 V – 3.6 V

ABSOLUTE MAXIMUM RATINGS

over operating junction temperature range (unless otherwise noted) (1)

Supply voltage range, V_{DD}	–0.5 V to 4.6 V
Input voltage range, V_I (2) (3)	–0.5 V to V_{DD} + 0.5 V
Output voltage range, V_O (2) (3)	–0.5 V to V_{DD} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I> V_{DD})	±50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{DD})	±50 mA
Continuous total output current, I_O (V_O = 0 to V_{DD})	±50 mA
Storage temperature range T_{stg}	–65°C to 150°C

(1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output negative voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(3) This value is limited to 4.6 V maximum.

THERMAL INFORMATION

THERMAL METRIC[1]		CDCVF2310 PW 24 PINS	UNITS
θ_{JA}	Junction-to-ambient thermal resistance[2]	91.7	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance[3]	31.2	
θ_{JB}	Junction-to-board thermal resistance[4]	46.4	
ψ_{JT}	Junction-to-top characterization parameter[5]	1.5	
ψ_{JB}	Junction-to-board characterization parameter[6]	45.8	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance[7]	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
(5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
(6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).
(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

RECOMMENDED OPERATING CONDITIONS [1]

		MIN	NOM	MAX	UNIT
Supply voltage, V_{DD}		2.3	2.5		V
			3.3	3.6	
Low-level input voltage, V_{IL}	V_{DD} = 3 V to 3.6 V			0.8	V
	V_{DD} = 2.3 V to 2.7 V			0.7	
High-level input voltage, V_{IH}	V_{DD} = 3 V to 3.6 V	2			V
	V_{DD} = 2.3 V to 2.7 V	1.7			
Input voltage, V_I		0		V_{DD}	V
High-level output current, I_{OH}	V_{DD} = 3 V to 3.6 V			12	mA
	V_{DD} = 2.3 V to 2.7 V			6	
Low-level output current, I_{OL}	V_{DD} = 3 V to 3.6 V			12	mA
	V_{DD} = 2.3 V to 2.7 V			6	
Operating junction temperature, T_J		–55		125	°C

(1) Unused inputs must be held high or low to prevent them from floating.

ELECTRICAL CHARACTERISTICS

over recommended operating junction temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP(1)	MAX	UNIT
V_{IK}	Input voltage	V_{DD} = 3 V,	I_I = –18 mA			–1.2	V
I_I	Input current	V_I = 0 V or V_{DD}				±5	µA
I_{DD} (2)	Static device current	CLK = 0 V or V_{DD},	I_O = 0 mA			100	µA
C_I	Input capacitance	V_{DD} = 2.3 V to 3.6 V,	V_I = 0 V or V_{DD}		2.5		pF
C_O	Output capacitance	V_{DD} = 2.3 V to 3.6 V,	V_I = 0 V or V_{DD}		2.8		pF
V_{DD} = 3.3 V ±0.3 V							
V_{OH}	High-level output voltage	V_{DD} = min to max,	I_{OH} = –100 µA	V_{DD} – 0.2			V
		V_{DD} = 3 V	I_{OH} = –12 mA	2.1			
			I_{OH} = –6 mA	2.4			
V_{OL}	Low-level output voltage	V_{DD} = min to max,	I_{OL} = –100 µA			0.2	V
		V_{DD} = 3 V	I_{OL} = 12 mA			0.8	
			I_{OL} = 6 mA			0.55	
I_{OH}	High-level output current	V_{DD} = 3 V,	V_O = 1 V	–28			mA
		V_{DD} = 3.3 V,	V_O = 1.65 V		–36		
		V_{DD} = 3.6 V,	V_O = 3.135 V			–14	
I_{OL}	Low-level output current	V_{DD} = 3 V,	V_O = 1.95 V	28			mA
		V_{DD} = 3.3 V,	V_O = 1.65 V		36		
		V_{DD} = 3.6 V,	V_O = 0.4 V			14	
V_{DD} = 2.5 V ±0.2 V							
V_{OH}	High-level output voltage	V_{DD} = min to max,	I_{OH} = –100 µA	V_{DD} – 0.2			V
		V_{DD} = 2.3 V	I_{OH} = –6 mA	1.8			
V_{OL}	Low-level output voltage	V_{DD} = min to max,	I_{OL} = 100 µA			0.2	V
		V_{DD} = 2.3 V	I_{OL} = 6 mA			0.55	
I_{OH}	High-level output current	V_{DD} = 2.3 V,	V_O = 1 V	–15			mA
		V_{DD} = 2.5 V,	V_O = 1.25 V		–25		
		V_{DD} = 2.7 V,	V_O = 2.375 V			–10	
I_{OL}	Low-level output current	V_{DD} = 2.3 V,	V_O = 1.2 V	15			mA
		V_{DD} = 2.5 V,	V_O = 1.25 V		25		
		V_{DD} = 2.7 V,	V_O = 0.3 V			10	

(1) All typical values are at respective nominal V_{DD}.
(2) For I_{CC} over frequency, see Figure 6.

TIMING REQUIREMENTS

over recommended ranges of supply voltage and operating junction temperature

			MIN	NOM	MAX	UNIT
f_{clk}	Clock frequency	V_{DD} = 3 V to 3.6 V	0		200	MHz
		V_{DD} = 2.3 V to 2.7 V	0		170	

JITTER CHARACTERISTICS

Characterized using CDCVF2310 Performance EVM when V_{DD}=3.3 V. Outputs not under test are terminated to 50 Ω.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{jitter}	Additive phase jitter from input to output 1Y0	12 kHz to 5 MHz, f_{out} = 30.72 MHz		52		fs rms
		12 kHz to 20 MHz, f_{out} = 125 MHz		45		

SWITCHING CHARACTERISTICS

over recommended operating junction temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{DD} = 3.3 V ±0.3 V (see Figure 2)						
t_{PLH} / t_{PHL}	CLK to Yn	f = 0 MHz to 200 MHz For circuit load, see Figure 2.	1.3		3.3	ns
$t_{sk(o)}$	Output skew (Ym to Yn) (1) (see Figure 4)				100	ps
$t_{sk(p)}$	Pulse skew (see Figure 5)				570	ps
$t_{sk(pp)}$	Part-to-part skew				500	ps
t_r	Rise time (see Figure 3)	V_O = 0.4 V to 2 V	0.7		2.2	V/ns
t_f	Fall time (see Figure 3)	V_O = 2 V to 0.4 V	0.7		2.2	V/ns
$t_{su(en)}$	Enable setup time, G_high before CLK ↓		0.1			ns
$t_{su(dis)}$	Disable setup time, G_low before CLK ↓		0.1			ns
$t_{h(en)}$	Enable hold time, G_high after CLK ↓		0.4			ns
$t_{h(dis)}$	Disable hold time, G_low after CLK ↓		0.4			ns
V_{DD} = 2.5 V ±0.2 V (see Figure 2)						
t_{PLH} / t_{PHL}	CLK to Yn	f = 0 MHz to 170 MHz For circuit load, see Figure 2.	1.5		4	ns
$t_{sk(o)}$	Output skew (Ym to Yn) (1) (see Figure 4)				170	ps
$t_{sk(p)}$	Pulse skew (see Figure 5)				680	ps
$t_{sk(pp)}$	Part-to-part skew				600	ps
t_r	Rise time (see Figure 3)	V_O = 0.4 V to 1.7 V	0.5		1.4	V/ns
t_f	Fall time (see Figure 3)	V_O = 1.7 V to 0.4 V	0.5		1.4	V/ns
$t_{su(en)}$	Enable setup time, G_high before CLK ↓		0.1			ns
$t_{su(dis)}$	Disable setup time, G_low before CLK ↓		0.1			ns
$t_{h(en)}$	Enable hold time, G_high after CLK ↓		0.4			ns
$t_{h(dis)}$	Disable hold time, G_low after CLK ↓		0.4			ns

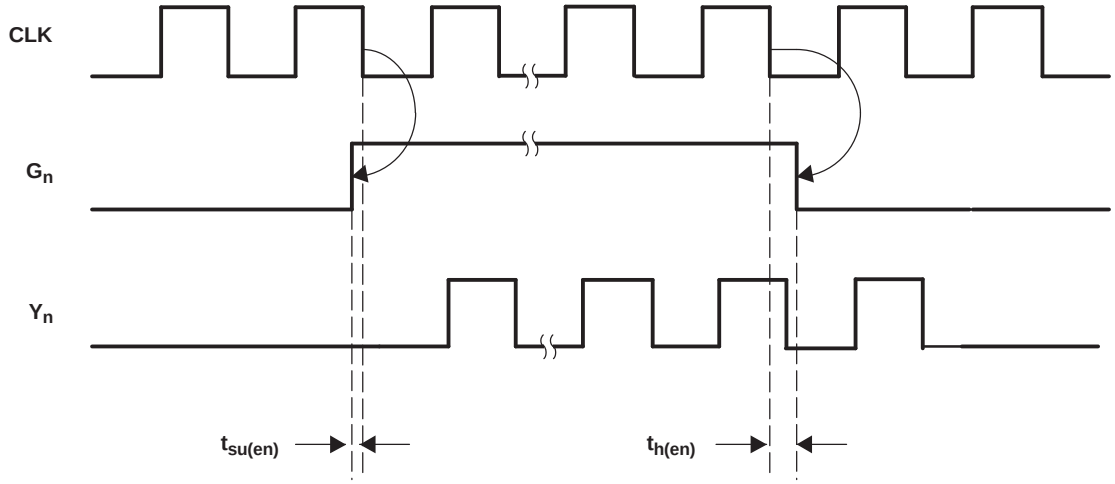
(1) The $t_{sk(o)}$ specification is only valid for equal loading of all outputs.

DETAILED DESCRIPTION

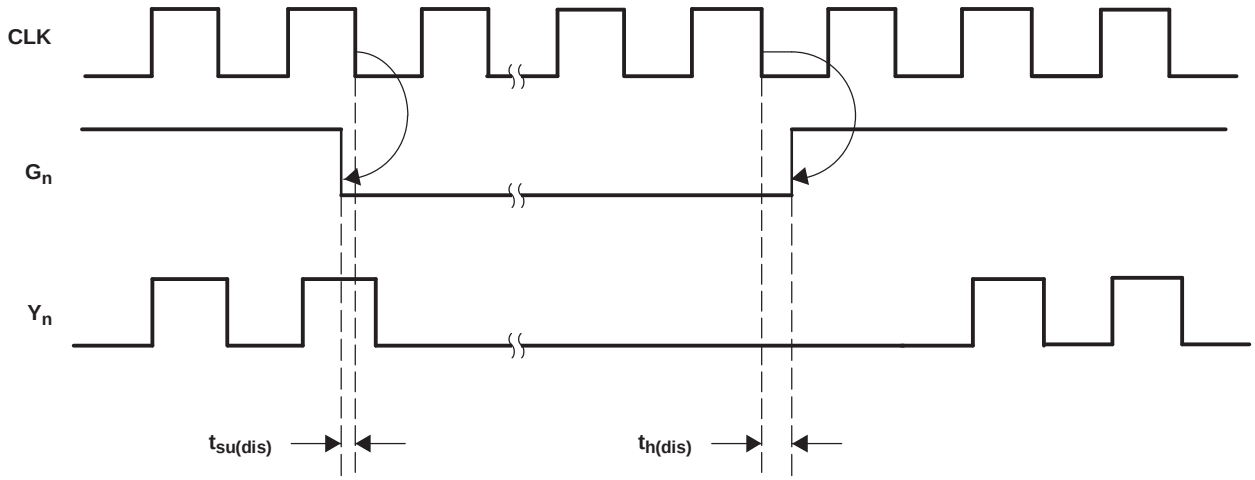
Output Enable Glitch Suppression Circuit

The purpose of the glitch suppression circuitry is to ensure the output enable sequence is synchronized with the clock input such that the output buffer is enabled or disabled on the next full period of the input clock (negative edge triggered by the input clock) (see Figure 1).

The G input must fulfill the timing requirements (t_{su}, t_h) according to the *Switching Characteristics* table for predictable operation.



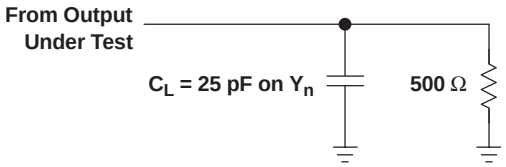
a) Enable Mode



b) Disable Mode

Figure 1. Enable and Disable Mode Relative to CLK↓

PARAMETER MEASUREMENT INFORMATION



A. C_L includes probe and jig capacitance.

B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 200 MHz, Z_O = 50 Ω, t_r < 1.2 ns, t_f < 1.2 ns.

Figure 2. Test Load Circuit

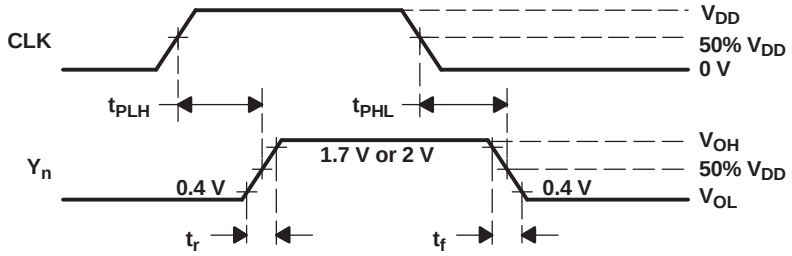


Figure 3. Voltage Waveforms Propagation Delay Times

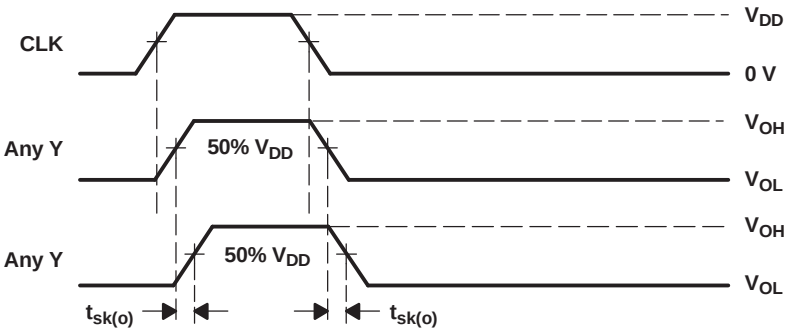
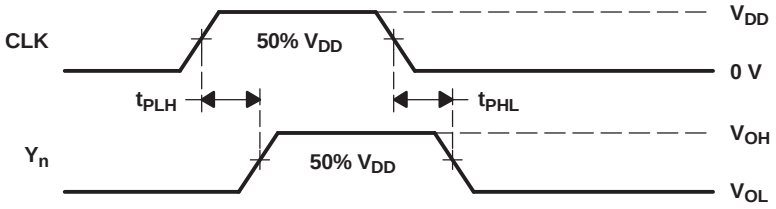


Figure 4. Output Skew



NOTE: $t_{sk(p)} = | t_{PLH} - t_{PHL} |$

Figure 5. Pulse Skew

PARAMETER MEASUREMENT INFORMATION (continued)

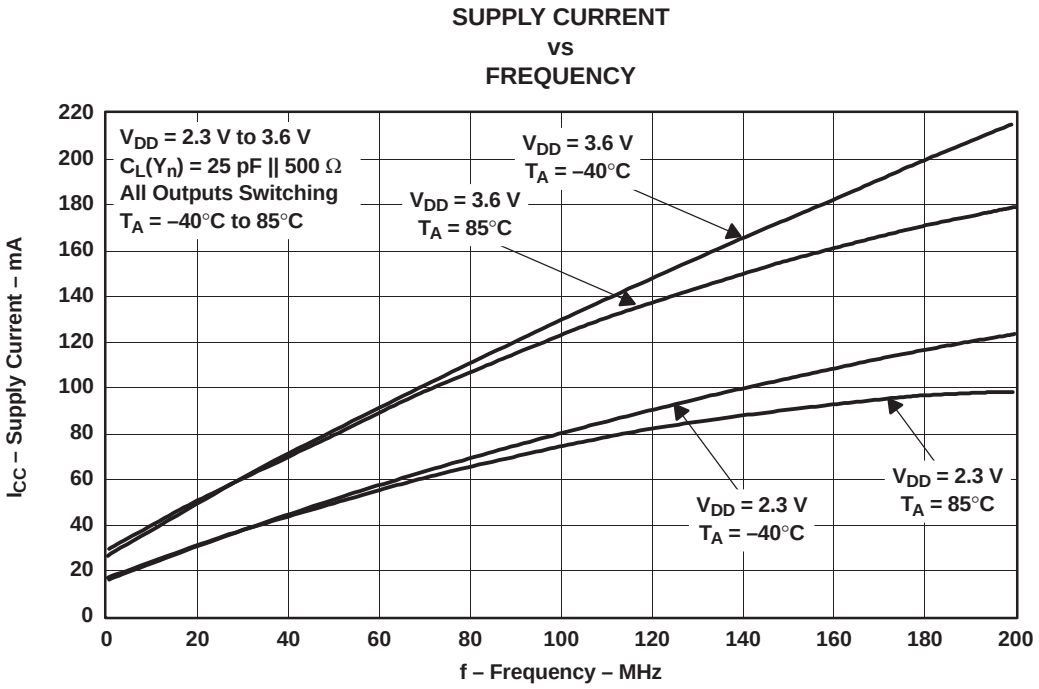


Figure 6.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
CDCVF2310MPWEP	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples
CDCVF2310MPWREP	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples
V62/13603-01XE	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples
V62/13603-01XE-T	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

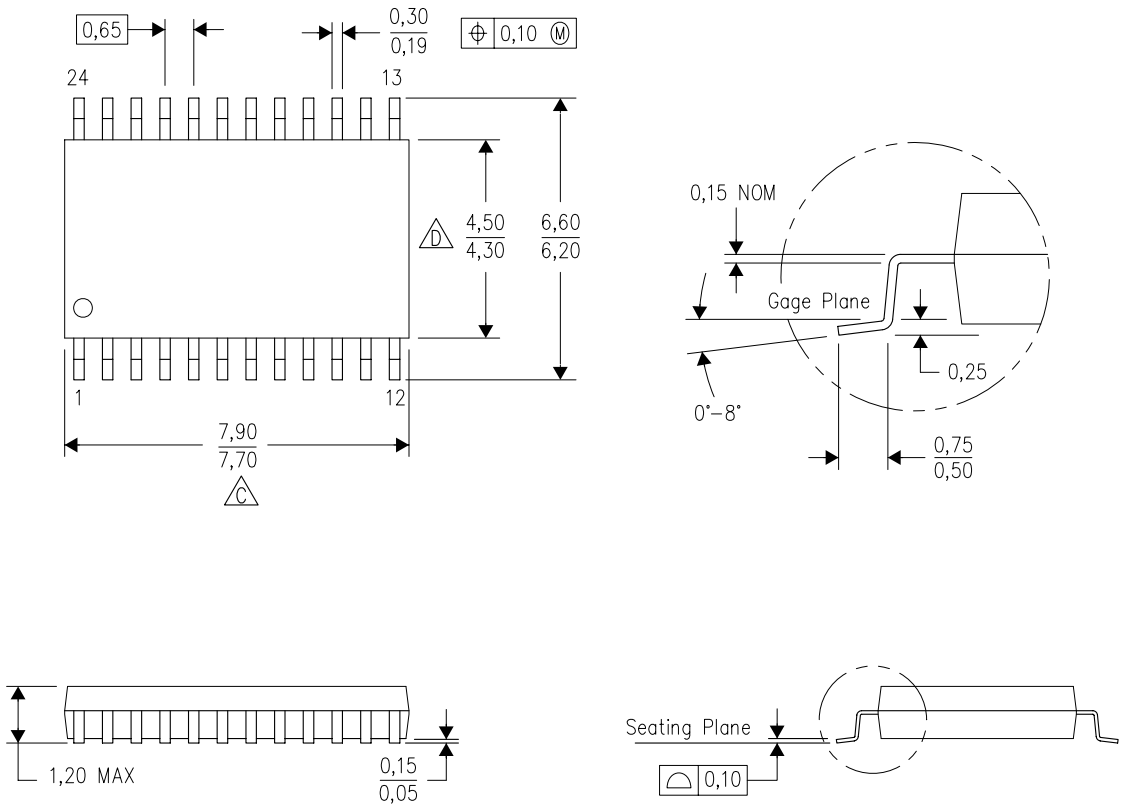
OTHER QUALIFIED VERSIONS OF CDCVF2310-EP :

- Catalog: CDCVF2310

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

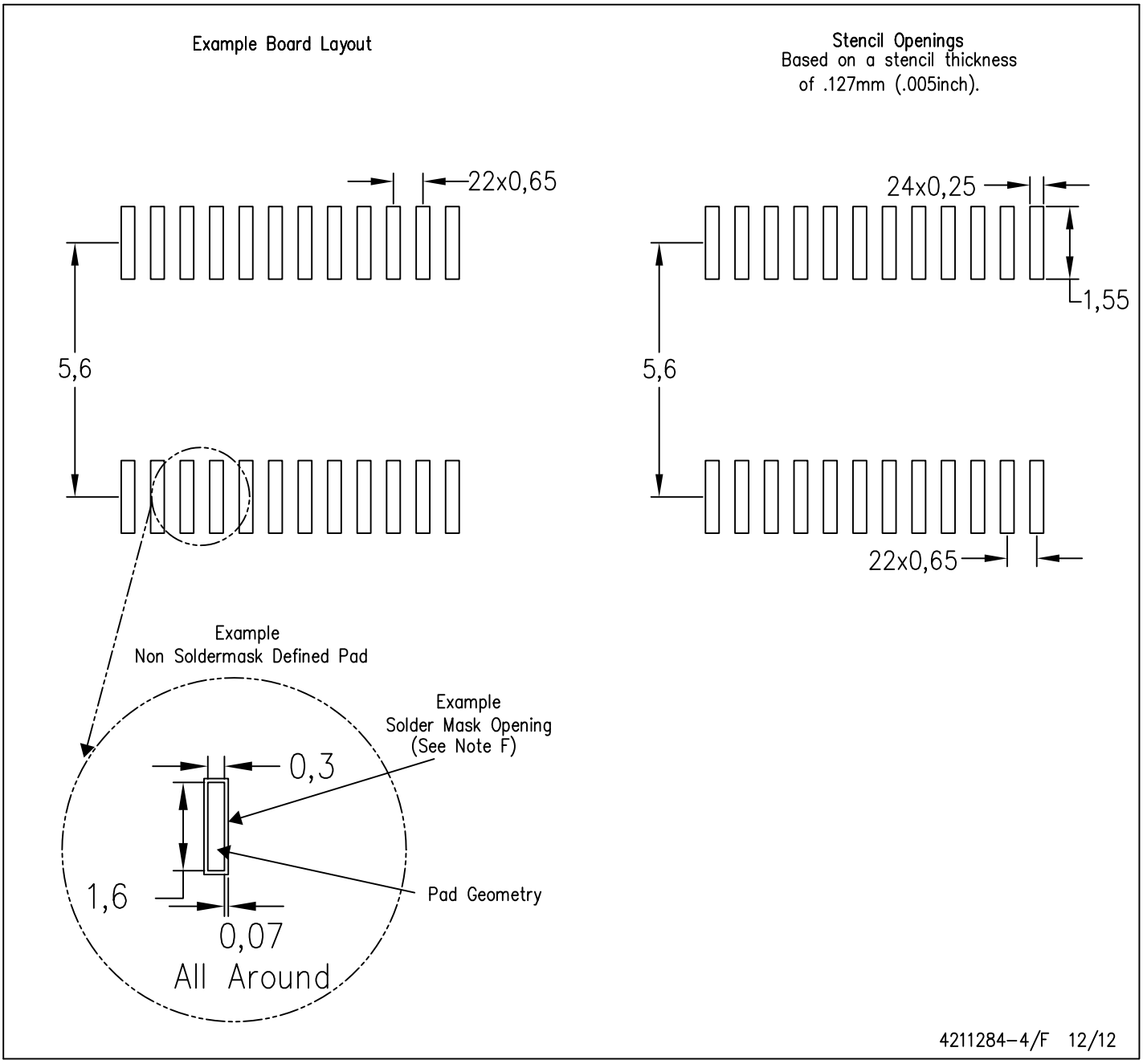
PW (R–PDSO–G24) PLASTIC SMALL OUTLINE



4040064–6/G 02/11

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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Products		**Applications**	
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